High-Power NPN Silicon Transistors

... designed for use in industrial-military power amplifier and switching circuit applications.

• High Collector-Emitter Sustaining Voltage -

• High DC Current Gain -

$$h_{FE} = 30 - 120 @ I_C = 10 Adc$$

= 12 (Min) @ $I_C = 25 Adc$

• Low Collector-Emitter Saturation Voltage -

$$V_{CE(sat)} = 1.0 \text{ Vdc (Max)} @ I_C = 10 \text{ Adc}$$

• Fast Switching Times @ $I_C = 10$ Adc

 $t_r = 0.3 \text{ ms (Max)}$

 $t_s = 1.0 \text{ ms (Max)}$

 $t_f = 0.25 \text{ ms (Max)}$

• Pb-Free Packages are Available

*MAXIMUM RATINGS

Rating	Symbol	2N6338	2N6341	Unit	
Collector-Base Voltage	V _{CB}	120	180	Vdc	
Collector-Emitter Voltage	V _{CEO}	100	150	Vdc	
Emitter-Base Voltage	V _{EB}	6	.0.0	Vdo	
Collector Current Continuous Peak	O.	2 5	Adc		
Base Current	JB	C 10		Adc	
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD		00 14	W W/°C	
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200		°C	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	0.875	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability. *Indicates JEDEC Registered Data.



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25 AMPERE POWER TRANSISTORS NPN SILICON



TO-204AA CASE 1-07

ORDERING INFORMATION

Device	Package	Shipping
2N6338	TO-204AA	100 Units / Tray
2N6338G	TO-204AA (Pb-Free)	100 Units / Tray
2N6341	TO-204AA	100 Units / Tray
2N6341G	TO-204AA (Pb-Free)	100 Units / Tray

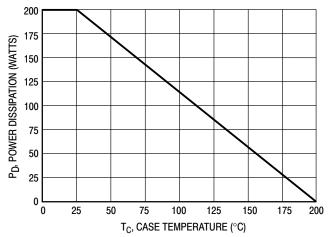


Figure 1. Power Derating



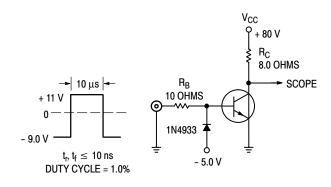
*ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

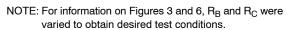
Characteristic			Min	Max	Unit	
OFF CHARACTERISTICS						
3 3 ()	N6338 N6341	V _{CEO(sus)}	100 150	- -	Vdc	
(OL , B ,	N6338 N6341	I _{CEO}	- -	50 50	μAdc	
Collector Cutoff Current $(V_{CE} = Rated\ V_{CEO},\ V_{EB(off)} = 1.5\ Vdc)$ $(V_{CE} = Rated\ V_{CEO},\ V_{EB(off)} = 1.5\ Vdc,\ T_{C} = 150^{\circ}C)$		I _{CEX}	- -	10 1.0	μAdc mAdc	
Collector Cutoff Current (V _{CB} = Rated V _{CB} , I _E = 0)		I _{CBO}	-	10	μAdc	
Emitter Cutoff Current (V _{BE} = 6.0 Vdc, I _C = 0)		I _{EBO}	-	100	μAdc	
ON CHARACTERISTICS (1)						
DC Current Gain) $ \begin{aligned} &(I_C=0.5 \text{ Adc, V}_{CE}=2.0 \text{ Vdc}) \\ &(I_C=10 \text{ Adc, V}_{CE}=2.0 \text{ Vdc}) \\ &(I_C=25 \text{ Adc, V}_{CE}=2.0 \text{ Vdc}) \end{aligned} $		h _{FE}	50 30 12	- 120 -	-	
Collector Emitter Saturation Voltage $(I_C = 10 \text{ Adc}, I_B = 1.0 \text{ Adc})$ $(I_C = 25 \text{ Adc}, I_B = 2.5 \text{ Adc})$		V _{CE(sat)}		1.0 1.8	Vdc	
Base–Emitter Saturation Voltage $(I_C = 10 \text{ Adc}, I_B = 1.0 \text{ Adc})$ $(I_C = 25 \text{ Adc}, I_B = 2.5 \text{ Adc})$		V _{BE(sat)}	- -	1.8 2.5	Vdc	
Base-Emitter On Voltage (I _C = 10 Adc, V _{CE} = 2.0 Vdc)		V _{BE(on)}	-	1.8	Vdc	
DYNAMIC CHARACTERISTICS	<u> </u>		•	•	•	
Current-Gain - Bandwidth Product (2) $(I_C = 1.0 \text{ Adc}, V_{CE} = 10 \text{ Vdc}, f_{test} = 10 \text{ Ndc})$	ИHz)	f _T	40	_	MHz	
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 0.1 MHz)		C _{ob}	-	300	pF	
SWITCHING CHARACTERISTICS	'			•	•	
Rise Time (V _{CC} ≈ 80 Vdc, I _C = 10Adc, I _{B1} = 1.0 Adc, V _{BE(off)} = 6.0 Vdc)		t _r	_	0.3	μѕ	

Rise Time ($V_{CC} \approx 80 \text{ Vdc}$, $I_C = 10 \text{Adc}$, $I_{B1} = 1.0 \text{ Adc}$, $V_{BE(off)} = 6.0 \text{ Vdc}$) 1.0 Storage Time ($V_{CC} \approx 80$ Vdc, $I_{C} = 10$ Adc, $I_{B1} = I_{B2} = 1.0$ Adc) t_s μs Fall Time ($V_{CC} \approx 80 \text{ Vdc}$, $I_C = 10 \text{ Adc}$, $I_{B1} = I_{B2} = 1.0 \text{ Adc}$) 0.25 t_f μs

^{*}Indicates JEDEC Registered Data. (1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

⁽²⁾ $f_T = |h_{fe}| \bullet f_{test}$.





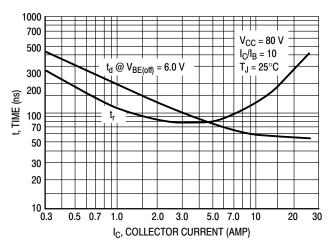
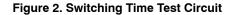


Figure 3. Turn-On Time



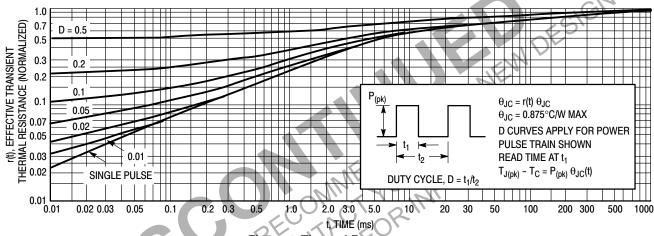


Figure 4. Thermal Response

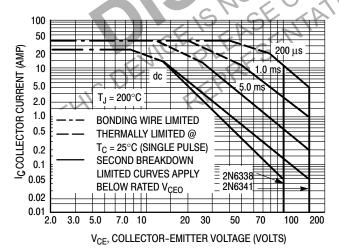
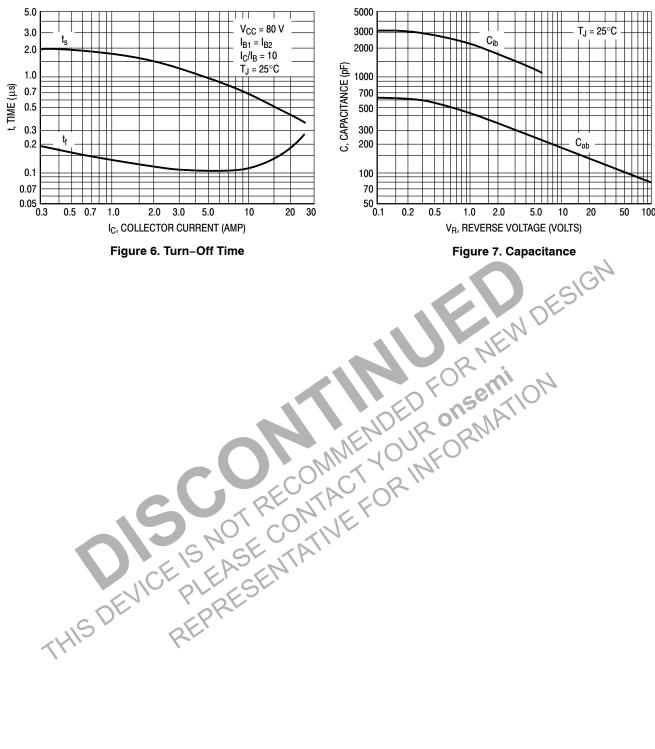
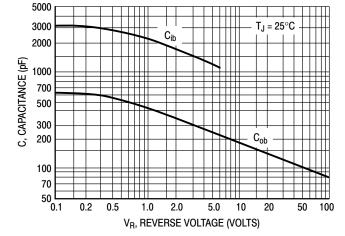


Figure 5. Active Region Safe Operating Area

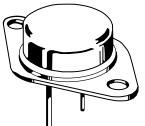
There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 200^{\circ}\text{C}$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 200^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.





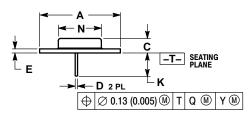


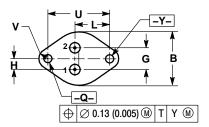


TO-204 (TO-3) **CASE 1-07 ISSUE Z**

DATE 05/18/1988







- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.550 REF		39.37 REF		
В		1.050		26.67	
С	0.250	0.335	6.35	8.51	
D	0.038	0.043	0.97	1.09	
Е	0.055	0.070	1.40	1.77	
G	0.430 BSC		10.92 BSC		
Н	0.215 BSC		5.46	5.46 BSC	
K	0.440	0.480	11.18	12.19	
L	0.665 BSC		16.89	BSC	
N		0.830		21.08	
Q	0.151	0.165	3.84	4.19	
U	1.187 BSC		30.15	15 BSC	
٧	0.131	0.188	3.33	4.77	

STYLE I:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. BASE	PIN 1. GATE	PIN 1. GROUND	PIN 1. CATHODE
2. EMITTER	2. COLLECTOR	2. SOURCE	2. INPUT	2. EXTERNAL TRIP/DELAY
CASE: COLLECTOR	CASE: EMITTER	CASE: DRAIN	CASE: OUTPUT	CASE: ANODE
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	
PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE #1	PIN 1. ANODE #1	
2. EMITTER	2. OPEN	2. CATHODE #2	ANODE #2	
CASE: COLLECTOR	CASE: CATHODE	CASE: ANODE	CASE: CATHODE	

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